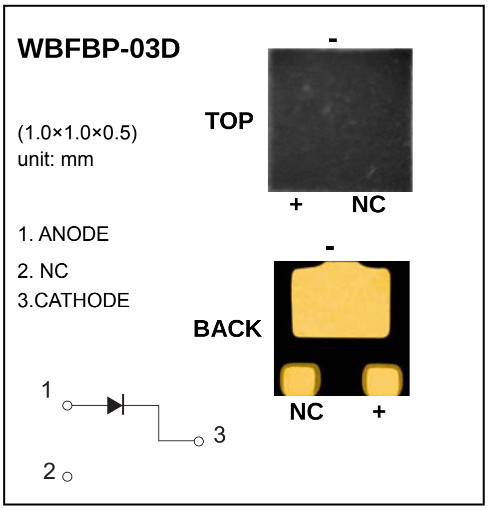
JCST

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03D Plastic-Encapsulate Diodes



WBFBP-03D

(1.0×1.0×0.5)
unit: mm

1. ANODE
2. NC
3.CATHODE

DK914LLD03 SWITCHING DIODE

DESCRIPTION

Epitaxial planar silicon diode

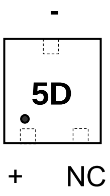
FEATURES

Fast Switching Speed
Ultra-Small Surface Mount Package
For General Purpose Switching Applications
High Conductance
Lead Free Product

APPLICATION

High Conductance Ultra Fast Diode
For Portable Equipment:(i.e. Mobile Phone,MP3, MD,CD-ROM, DVD-ROM, Note Book PC, etc.)

MARKING: **5D**



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25℃

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage **Working Peak Reverse Voltage** **DC Blocking Voltage**	V_{RRM} V_{RWM} V_R	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	500	mA
Average Rectified Output Current	I_O	300	mA
Power Dissipation	P_D	100	mW
Junction Temperature	T_j	150	℃
Storage Temperature	T_{STG}	-55~+150	℃

Electrical Ratings @Ta=25℃

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V_{F1}			0.715	V	I_F=1mA
	V_{F2}			0.855	V	I_F=10mA
	V_{F3}			1.0	V	I_F=50mA
	V_{F4}			1.25	V	I_F=150mA
Reverse current	I_{R1}			1	μA	V_R=75V
	I_{R2}			25	nA	V_R=20V
Capacitance between terminals	C_T			2	pF	V_R=0,f=1MHz
Reverse recovery time	t_{rr}			4	ns	I_F=I_R=10mA,I_{rr}=0.1XI_R